



#### **DUAL P-CHANNEL ENHANCEMENT MODE MOSFET**

## **Product Summary**

BV <sub>DSS</sub>	R <sub>DS(ON)</sub>	I <sub>D</sub> T <sub>A</sub> = +25°C
-30V	$95m\Omega @ V_{GS} = -10V$	-2.8A
-30 V	140mΩ @ V <sub>GS</sub> = -4.5V	-2.3A

## **Description**

This new generation MOSFET is designed to minimize the on-state resistance (R<sub>DS(ON)</sub>) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

## **Applications**

- Backlighting
- DC-DC Converters
- Power Management Functions

# **Features and Benefits**

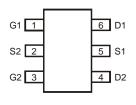
- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

## **Mechanical Data**

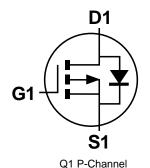
- Case: TSOT26
- Case Material: Molded Plastic, "Green" Molding Compound.
   UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals Connections: See Diagram
- Terminals: Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.013 grams (Approximate)

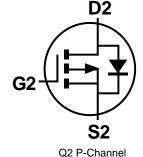
# TSOT26





Top View





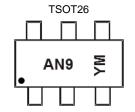
### **Ordering Information (Note 4)**

Part Number	Case	Packaging
DMP3164LVT-7	TSOT26	3,000 / Tape & Reel
DMP3164LVT-13	TSOT26	10,000 / Tape & Reel

Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.

- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

# **Marking Information**



AN9 = Product Type Marking Code YM = Date Code Marking  $\overline{Y}$  = Year (ex: G = 2019) M = Month (ex: 9 = September)

Date Code Key

Year	2019	9	2020		2021	20	22	2023		2024	2	2025
Code	G		Н			,	J	K		L		M
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



# **Maximum Ratings** ( $@T_A = +25^{\circ}C$ , unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain-Source Voltage	$V_{DSS}$	-30	V
Gate-Source Voltage	V <sub>GSS</sub>	±12	V
Continuous Drain Current (Note 6) V <sub>GS</sub> = -4.5V	I <sub>D</sub>	-2.8 -2.2	А
Maximum Continuous Body Diode Forward Current (Note	Is	-1.0	Α
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I <sub>DM</sub>	-16	A

# Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	P <sub>D</sub>	0.83	W
Thermal Resistance, Junction to Ambient @T <sub>A</sub> = +25°C (Note 5)	$R_{\theta JA}$	151	°C/W
Power Dissipation (Note 6)	P <sub>D</sub>	1.16	W
Thermal Resistance, Junction to Ambient @T <sub>A</sub> = +25°C (Note 6)	R <sub>0JA</sub>	108	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

# Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

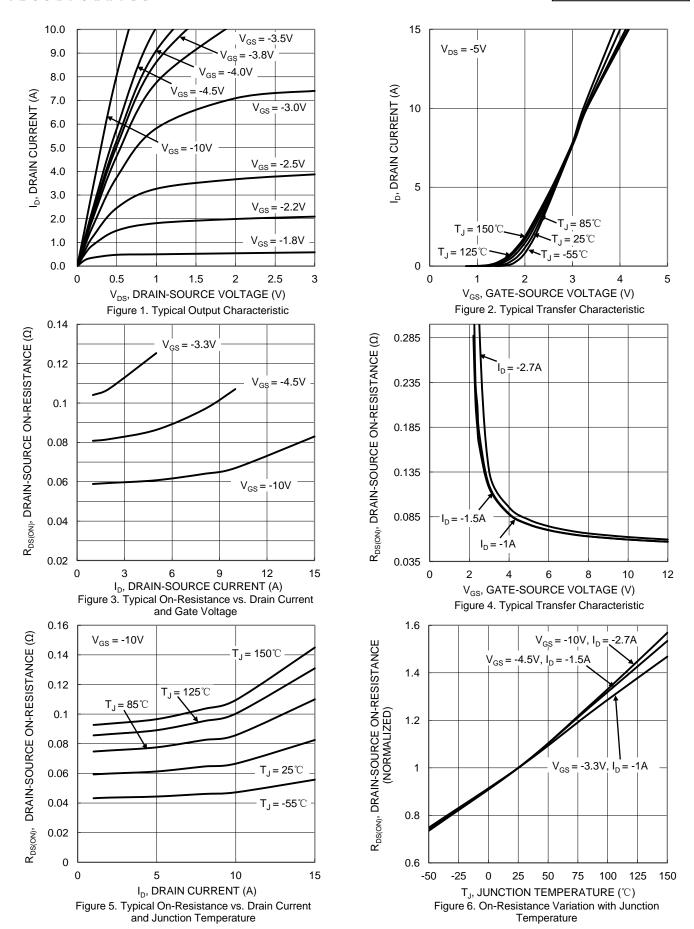
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)	- J		- 7 P				
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-30	_	_	V	$V_{GS} = 0V, I_D = -250\mu A$	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	_	_	-1.0	μΑ	$V_{DS} = -24V, V_{GS} = 0V$	
Gate-Source Leakage	I <sub>GSS</sub>	_	_	±100	nA	$V_{GS} = \pm 12V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	V <sub>GS(TH)</sub>	-0.7	-1.1	-2.1	V	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	
			60	95		$V_{GS} = -10V, I_D = -2.7A$	
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	_	81	140	mΩ	$V_{GS} = -4.5V, I_{D} = -1.5A$	
			104	300		$V_{GS} = -3.3V$ , $I_{D} = -1A$	
Diode Forward Voltage	$V_{SD}$		-0.8	-1.0	V	$V_{GS} = 0V, I_{S} = -1A$	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	C <sub>iss</sub>		324	_		V 45V V 0V	
Output Capacitance	Coss		44	_	pF	$V_{DS} = -15V, V_{GS} = 0V,$ f = 1.2MHz	
Reverse Transfer Capacitance	C <sub>rss</sub>	_	33	_			
Gate Resistance	Rq	_	7.2	_	Ω	$V_{DS} = 0V$ , $V_{GS} = 0V$ , $f = 1MHz$	
Total Gate Charge (V <sub>GS</sub> = -4.5V)	Qg	_	4.4	_		$V_{DS} = -15V, V_{GS} = -4.5V, I_{D} = -3A$	
Total Gate Charge (V <sub>GS</sub> = -10V)	Qq		8.6	_			
Gate-Source Charge	Qgs		0.3	_	nC	$V_{DS} = -15V$ , $V_{GS} = -10V$ , $I_{D} = -3A$	
Gate-Drain Charge	$Q_{gd}$		1.5	_			
Turn-On Delay Time	t <sub>D(ON)</sub>		7.7	_			
Turn-On Rise Time	t <sub>R</sub>		17.8	_		$V_{GS} = -10V, V_{DS} = -15V,$	
Turn-Off Delay Time	t <sub>D(OFF)</sub>		17.8	_	ns	$R_G = 6\Omega$ , $R_L = 15\Omega$	
Turn-Off Fall Time	t <sub>F</sub>	_	29.5	_			

Notes:

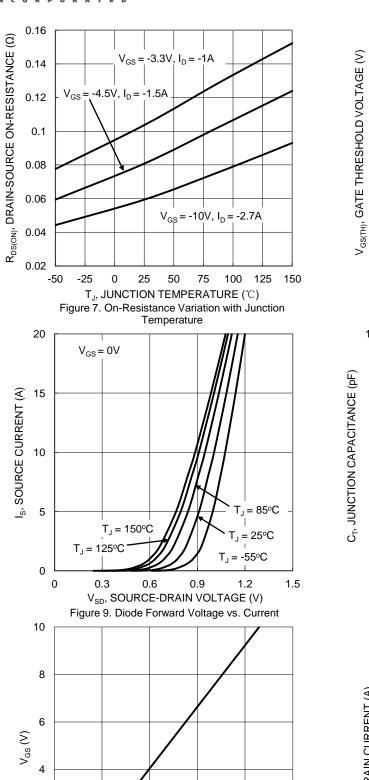
- 5. Device mounted on FR-4 substrate PCB, 2oz copper, with minimum recommended pad layout.
  6. Device mounted on FR-4 substrate PCB, 2oz copper, with 1inch square copper plate.
  7. Short duration pulse test used to minimize self-heating effect.

- 8. Guaranteed by design. Not subject to production testing.









 $V_{DS} = -15V, I_{D} = -3A$ 

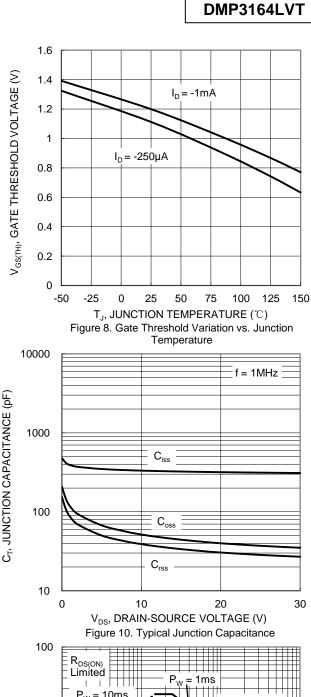
8

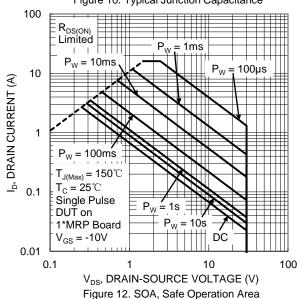
10

6

 $Q_q$  (nC)

Figure 11. Gate Charge





2

0

0

2



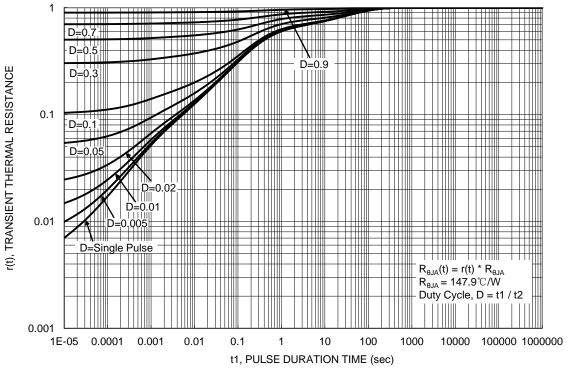


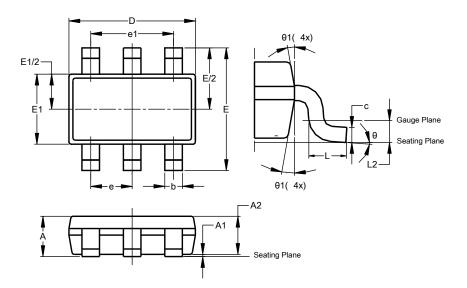
Figure 13. Transient Thermal Resistance



# **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### TSOT26

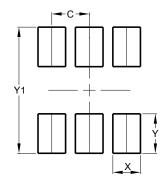


	TSOT26							
Dim	Min	Max	Тур					
Α	-	1.00	_					
A1	0.010	0.100	-					
A2	0.840	0.900	-					
D	2.800	3.000	2.900					
Е	2	2.800 BSC						
E1	1.500	1.700	1.600					
b	0.300	0.450	1					
С	0.120	0.200	1					
е	0.950 BSC							
e1	1	1.900 BSC						
L	0.30	0.50	-					
L2	0.250 BSC							
θ	0°	8°	4°					
θ1	4°	12°	-					
Δ	All Dimensions in mm							

# **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### TSOT26



Dimensions	Value (in mm)				
С	0.950				
Х	0.700				
Y	1.000				
Y1	3.199				



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